

ABSTRACT AMENDMENT

Replace the Abstract with:

~~The light-receiving~~ A gate oxide film covering a light-incident surface of a
photodiode ~~is covered with a gate oxide film. Through the gate oxide film is formed~~
includes an opening exposing a central region of the light-receiving light-incident surface
of the photodiode. ~~The formation of~~ After forming the opening is followed by forming in
the gate oxide film serving as a light-incident surface protecting film, an antireflection
film formed of silicon nitride film, which covers covering the light-receiving light-
incident surface of the photodiode, exposed from the opening, which has an end on a field
oxide film riding upon the gate oxide film, and reaching up to the position is deposited.
A side surface of the antireflection film is spaced by a predetermined distance away from
a the field oxide film that is adjacent to proximate the photodiode, and which has an end
on and that provides electrical isolation. Another side surface of the antireflection film
faces a transfer gate side riding upon the top of the device and is disposed on the gate
oxide film located in the vicinity of near the opening, and reaching up to the position.
That side surface of the antireflection film is spaced by a predetermined distance away
from a the transfer gate electrode that is adjacent the photodiode.